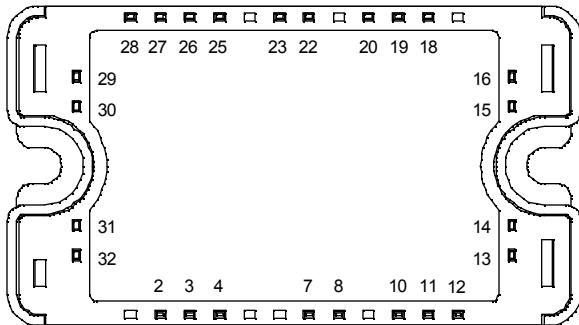
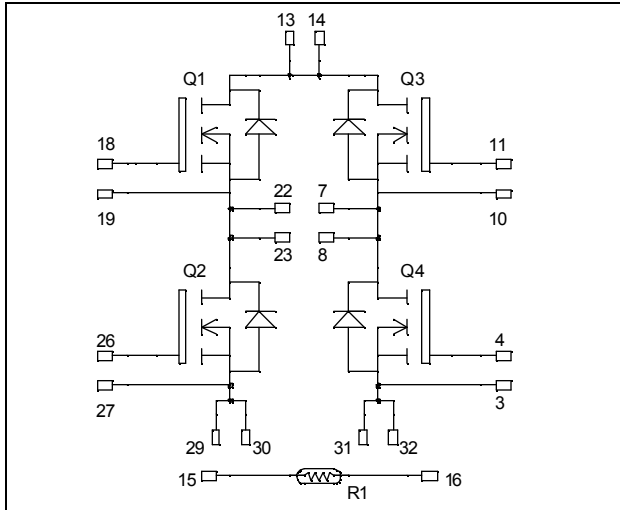


Full - Bridge MOSFET Power Module

$V_{DSS} = 500V$
 $R_{DSon} = 140m\Omega \text{ typ @ } T_j = 25^\circ C$
 $I_D = 26A \text{ @ } T_c = 25^\circ C$



All multiple inputs and outputs must be shorted together
 Example: 13/14 ; 29/30 ; 22/23 ...

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

Features

- Power MOS 7[®] FREDFETs
 - Low R_{DSon}
 - Low input and Miller capacitance
 - Low gate charge
 - Fast intrinsic reverse diode
 - Avalanche energy rated
 - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
 - Symmetrical design
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Each leg can be easily paralleled to achieve a phase leg of twice the current capability
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{DSS}	Drain - Source Breakdown Voltage	500	V
I_D	Continuous Drain Current	$T_c = 25^\circ C$	26
		$T_c = 80^\circ C$	18
I_{DM}	Pulsed Drain current	105	A
V_{GS}	Gate - Source Voltage	± 30	V
R_{DSon}	Drain - Source ON Resistance	168	$m\Omega$
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$	208
I_{AR}	Avalanche current (repetitive and non repetitive)	35	A
E_{AR}	Repetitive Avalanche Energy	30	mJ
E_{AS}	Single Pulse Avalanche Energy	1300	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0\text{V}, V_{DS} = 500\text{V}$			100	μA
		$V_{GS} = 0\text{V}, V_{DS} = 400\text{V}$			500	
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 10\text{V}, I_D = 13\text{A}$		140	168	$\text{m}\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 1\text{mA}$	3		5	V
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30\text{V}, V_{DS} = 0\text{V}$			± 100	nA

Dynamic Characteristics

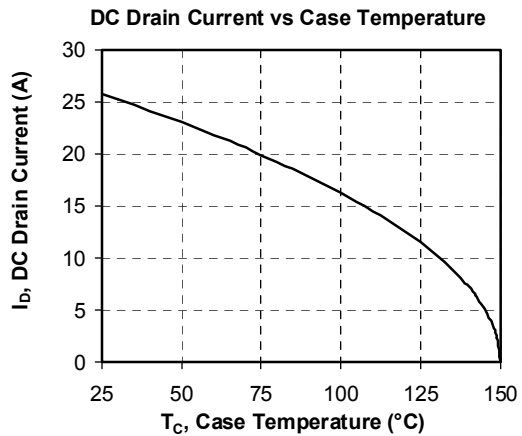
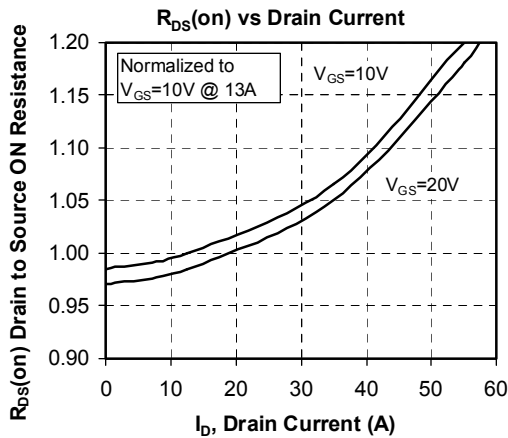
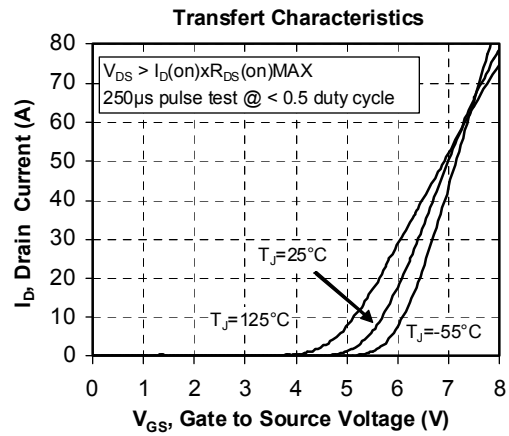
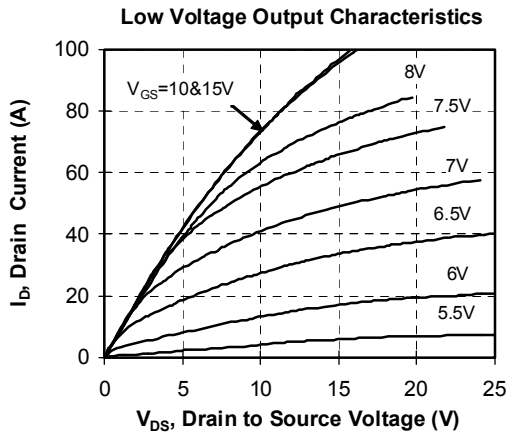
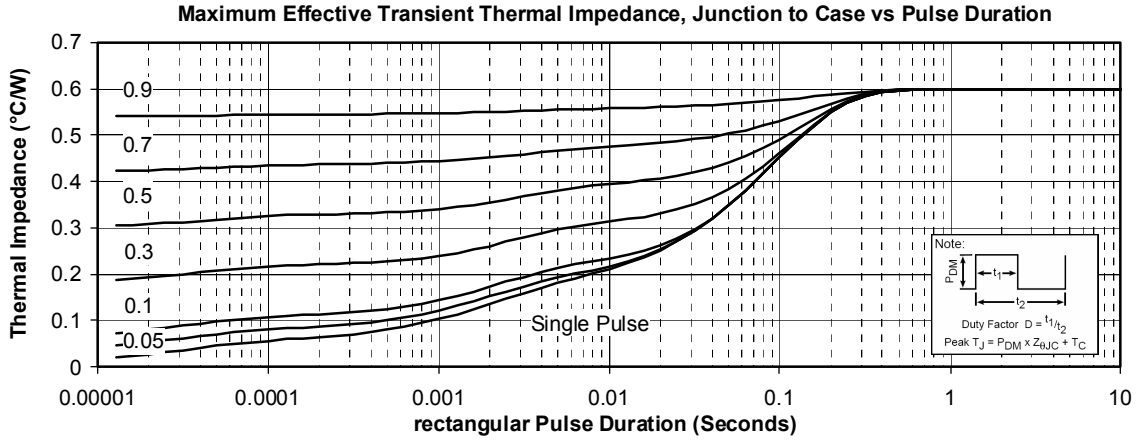
Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0\text{V}$		3259		pF
C_{oss}	Output Capacitance	$V_{DS} = 25\text{V}$		709		
C_{rss}	Reverse Transfer Capacitance	$f = 1\text{MHz}$		51		
Q_g	Total gate Charge	$V_{GS} = 10\text{V}$		72		nC
Q_{gs}	Gate – Source Charge	$V_{Bus} = 250\text{V}$		20		
Q_{gd}	Gate – Drain Charge	$I_D = 26\text{A}$		36		
$T_{d(on)}$	Turn-on Delay Time	Inductive switching @ 125°C $V_{GS} = 15\text{V}$ $V_{Bus} = 333\text{V}$ $I_D = 26\text{A}$ $R_G = 5\Omega$		10		ns
T_r	Rise Time			17		
$T_{d(off)}$	Turn-off Delay Time			50		
T_f	Fall Time			41		
E_{on}	Turn-on Switching Energy	Inductive switching @ 25°C $V_{GS} = 15\text{V}, V_{Bus} = 333\text{V}$ $I_D = 26\text{A}, R_G = 5\Omega$		326		μJ
E_{off}	Turn-off Switching Energy			250		
E_{on}	Turn-on Switching Energy	Inductive switching @ 125°C $V_{GS} = 15\text{V}, V_{Bus} = 333\text{V}$ $I_D = 26\text{A}, R_G = 5\Omega$		548		μJ
E_{off}	Turn-off Switching Energy			288		

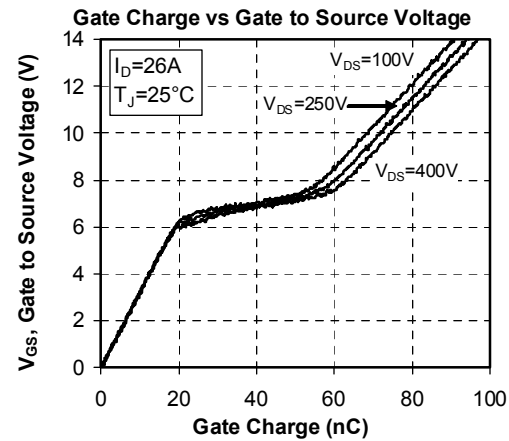
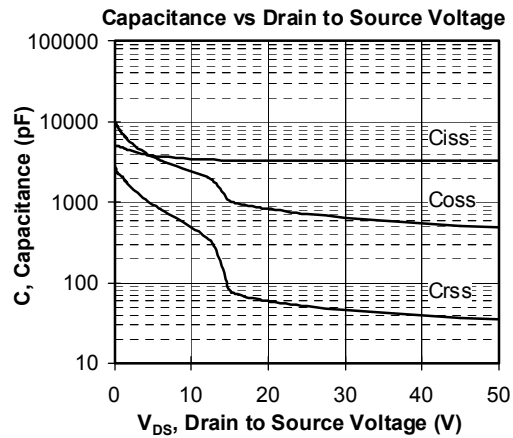
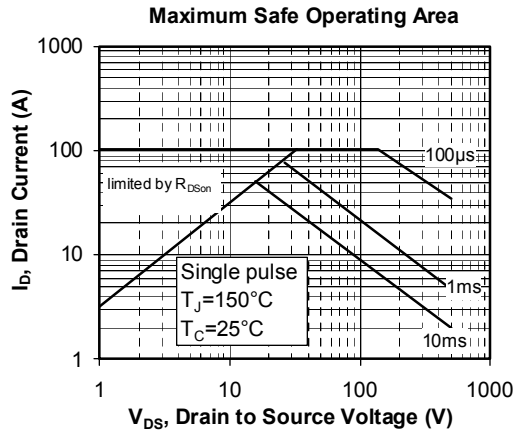
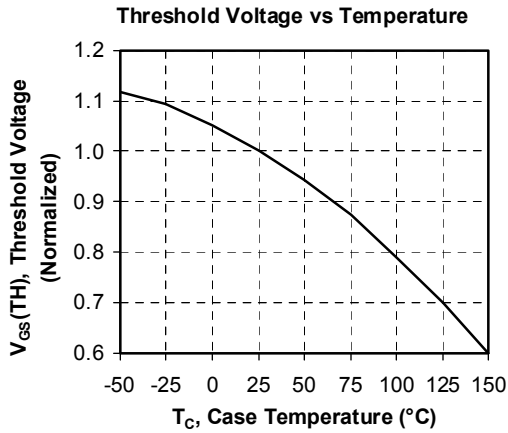
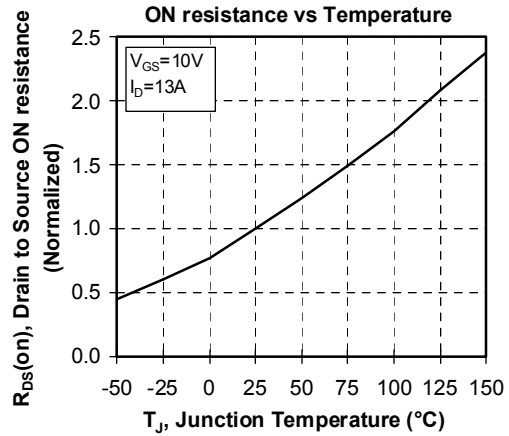
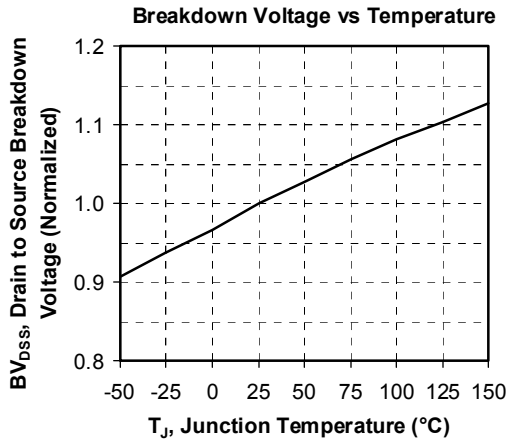
Source - Drain diode ratings and characteristics

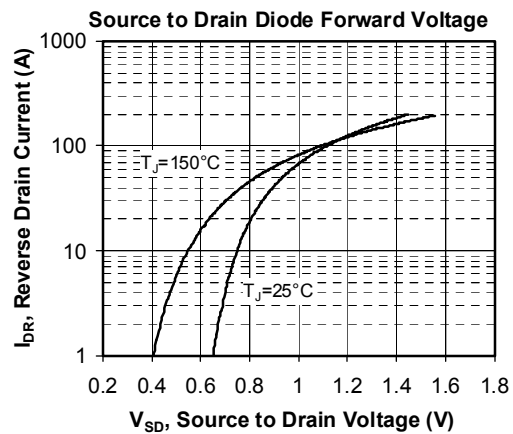
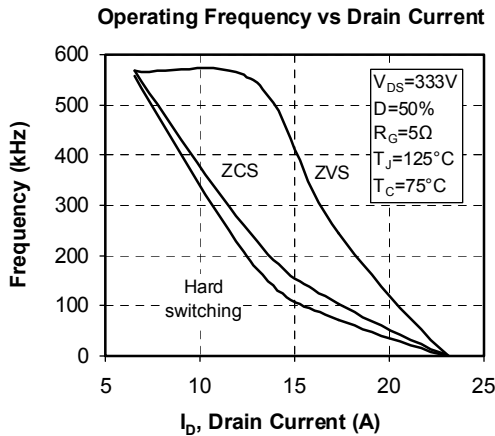
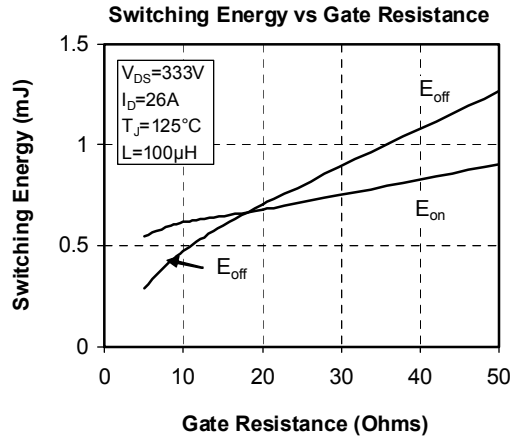
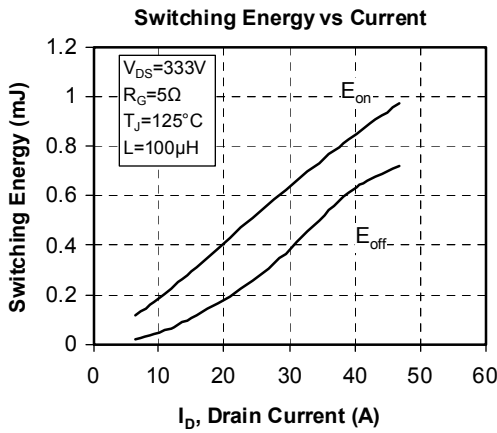
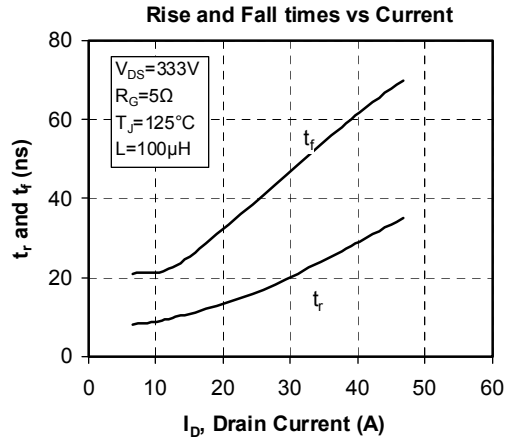
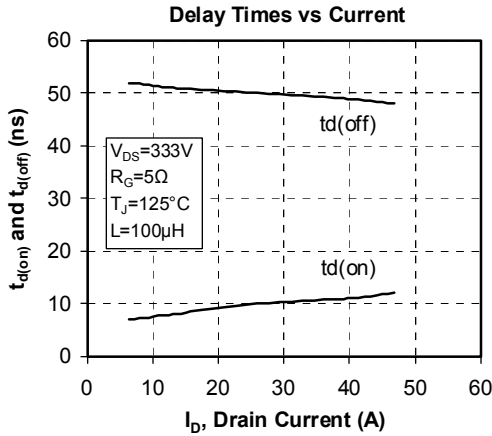
Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_S	Continuous Source current (Body diode)	$T_c = 25^\circ\text{C}$		26		A
		$T_c = 80^\circ\text{C}$		18		
V_{SD}	Diode Forward Voltage	$V_{GS} = 0\text{V}, I_S = -26\text{A}$			1.3	V
dv/dt	Peak Diode Recovery ①				15	V/ns
t_{rr}	Reverse Recovery Time	$I_S = -26\text{A}$ $V_R = 333\text{V}$ $di_s/dt = 100\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$		250	ns
			$T_j = 125^\circ\text{C}$		525	
Q_{rr}	Reverse Recovery Charge	$I_S = -26\text{A}$ $V_R = 333\text{V}$ $di_s/dt = 100\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$		1.6	μC
			$T_j = 125^\circ\text{C}$		6	

 ① dv/dt numbers reflect the limitations of the circuit rather than the device itself.

 $I_S \leq -26\text{A}$ $di/dt \leq 700\text{A}/\mu\text{s}$ $V_R \leq V_{DSS}$ $T_j \leq 150^\circ\text{C}$

Typical Performance Curve






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